AMENDMENTS TO THE CLAIMS

Claim 1 (Currently amended): A method of correcting
a mask layout, the mask layout comprising a plurality
5   of line patterns, the method comprising:
    providing line width deviation data of transferred
line patterns, the line width deviation comprising a
deviation   of   an   after-etch-inspection   critical
dimension of the transferred line patterns onto a wafer;
10   executing an inspection program to classify the line
patterns of the mask layout into at least a first-type
line pattern and a second-type line pattern according
to the line width deviation data of the transferred
line patternsa pattern density of the line patterns;
15   and
    making a line width correction of a first constant
value on the first-type line pattern and making a line
width correction of a second constant value on the
second-type line pattern;
20   wherein the first constant value is determined by
the line width deviation data of the first type line
pattern, and the second constant value is determined
by the line width deviation data of the second type
line pattern.
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Claim 2 (Original): The method of claim 1 wherein a
pattern density of the first-type line pattern is
different from a pattern density of the second-type
line pattern.
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Claim 3 (Original): The method of claim 2 wherein the
pattern density is determined by a distance between

2

two adjacent line patterns.

Claim 4 (Original): The method of claim 1 wherein the
line width deviation is a result of a systematic error.

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Claim 5(Original): The method of claim 1 wherein the
line width deviation is a result of a micro-loading
effect.

10   Claim 6 (Canceled)

Claim 7 (Original): The method of claim 1 wherein the
first-type line pattern comprises dense patterns or
semi-dense patterns, and the second-type line pattern
15   comprises isolated patterns.

Claim 8 (Original): The method of claim 1 wherein the
first-type line pattern comprises isolated patterns
or semi-isolated patterns, and the second-type line
20   pattern comprises dense patterns.

Claim 9 (Original): The method of claim 1 wherein the
line width correction of the first constant value and
the line width correction of the second constant value
25   comprise increasing line widths of the line patterns
or decreasing the line widths of the line patterns.

Claim 10 (Original): The method of claim 1 wherein each
of the line patterns is used for defining a conductive
30   area.

[[1.]] Claim 11 (Currently amended): A method of

3

correcting a mask layout, the mask layout comprising
a plurality of element patterns, the method comprising:
 providing pattern deviation data of transferred
element patterns, the pattern deviation comprising a
5   deviation of an after-etch-inspection critical
dimension of the transferred element patterns onto a
wafer;
     executing an inspection program to classify the
element patterns of the mask layout into at least a
10   first-type element pattern and a second-type element
pattern according to the pattern deviation dataa
pattern density of the transferred element patterns;
and
     making a selective correction on the first-type
15   element pattern and the second-type element pattern,
respectively;
     wherein the selective correction determines a
correction value on the first-type element pattern and
on the second-type element pattern according to the
20   pattern deviation data of the first-type element
pattern and of the second-type element pattern,
respectively.

1. Claim 12 (Currently amended): The method of claim
25   [[10]] 11 wherein the element patterns comprise line
patterns.

1. Claim 13 (Canceled)

30   1. Claim 14 (Currently amended): The method of claim
[[11]] 12 wherein the selective correction comprises
increasing line widths of the line patterns or

4

decreasing the line widths of the line patterns.

1. Claim 15 (Currently amended): The method of claim
[[10]] 11 wherein the pattern deviation is a result
5   of a systematic error.

1. Claim 16 (Currently amended): The method of claim
[[10]] 11 wherein the pattern deviation is a result
of a micro-loading effect.

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1. Claim 17 (Canceled)

1. Claim 18 (Currently amended): The method of claim
[[10]] 11 wherein the first-type element pattern
15 comprises dense patterns or semi-dense patterns, and
the second-type element pattern comprises isolated
patterns.

1. Claim 19 (Currently amended): The method of claim
20 [[10]] 11 wherein the first-type element pattern
comprises isolated patterns or semi-isolated patterns,
and the second-type element pattern comprises dense
patterns.

25 1. Claim 20 (Currently amended): The method of claim
[[10]] 11 wherein each of the element patterns is used
to define a conductive area.

Claims 21-29 (Canceled)
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5